Silicon Carbide Schottky Diode



VRRM =	1200 V
F (Tc = 135°C) =	64 A *
Qc =	214 nC *

#### Features

Advantages

- Low V<sub>F</sub> for High Temperature Operation
- Enhanced Surge and Avalanche Robustness
- Superior Figure of Merit Q<sub>C</sub>/I<sub>F</sub>
- Low Thermal Resistance
- Low Reverse Leakage Current
- Temperature Independent Fast Switching
- Positive Temperature Coefficient of V<sub>F</sub>
- High dV/dt Ruggedness

Improved System EfficiencyHigh System Reliability

• Optimal Price Performance

Reduced Cooling Requirements

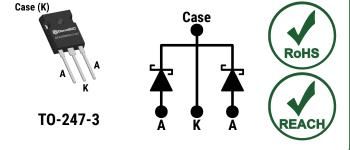
Zero Reverse Recovery Current

• Increased System Power Density

Enables Extremely Fast Switching

• Easy to Parallel without Thermal Runaway

## Package



### Applications

- Power Factor Correction (PFC)
- Electric Vehicles and Battery Chargers
- Solar Inverters
- High Frequency Converters
- Switched Mode Power Supply (SMPS)
- Motor Drives
- Anti-Parallel / Free-Wheeling Diode
- Induction Heating & Welding

#### Absolute Maximum Ratings (At Tc = 25°C Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values	Unit	Note
Repetitive Peak Reverse Voltage (Per Leg)	V <sub>RRM</sub>		1200	V	
		T <sub>C</sub> = 100°C, D = 1	46 / 92		
Continuous Forward Current (Per Leg / Per Device)	IF	T <sub>C</sub> = 135°C, D = 1	32 / 64	Α	Fig. 4
		T <sub>C</sub> = 157°C, D = 1	20 / 40		
Non-Repetitive Peak Forward Surge Current, Half Sine	Irou	T <sub>C</sub> = 25°C, t <sub>P</sub> = 10 ms	200	А	
Wave (Per Leg)	I <sub>F,SM</sub>	Tc = 150°C, t⊵ = 10 ms	160	A	
Repetitive Peak Forward Surge Current, Half Sine Wave	lenu	T <sub>C</sub> = 25°C, t <sub>P</sub> = 10 ms	120	А	
(Per Leg)	IF,RM	Tc = 150°C, t⊵ = 10 ms	84	A	
Non-Repetitive Peak Forward Surge Current (Per Leg)	I <sub>F,MAX</sub>	T <sub>C</sub> = 25°C, t <sub>P</sub> = 10 μs	1000	Α	
i²t Value (Per Leg)	∫i²dt	T <sub>C</sub> = 25°C, t <sub>P</sub> = 10 ms	200	A <sup>2</sup> s	
Non-Repetitive Avalanche Energy (Per Leg)	E <sub>AS</sub>	L = 1.8 mH, I <sub>AS</sub> = 20 A	360	mJ	
Diode Ruggedness (Per Leg)	dV/dt	V <sub>R</sub> = 0 ~ 960 V	200	V/ns	
Power Dissipation (Per Leg / Per Device)	Ртот	T <sub>C</sub> = 25°C	312 / 624	W	Fig. 3
Operating and Storage Temperature	T <sub>j</sub> , T <sub>stg</sub>		-55 to 175	°C	

\* Per Device



### **Electrical Characteristics (Per Leg)**

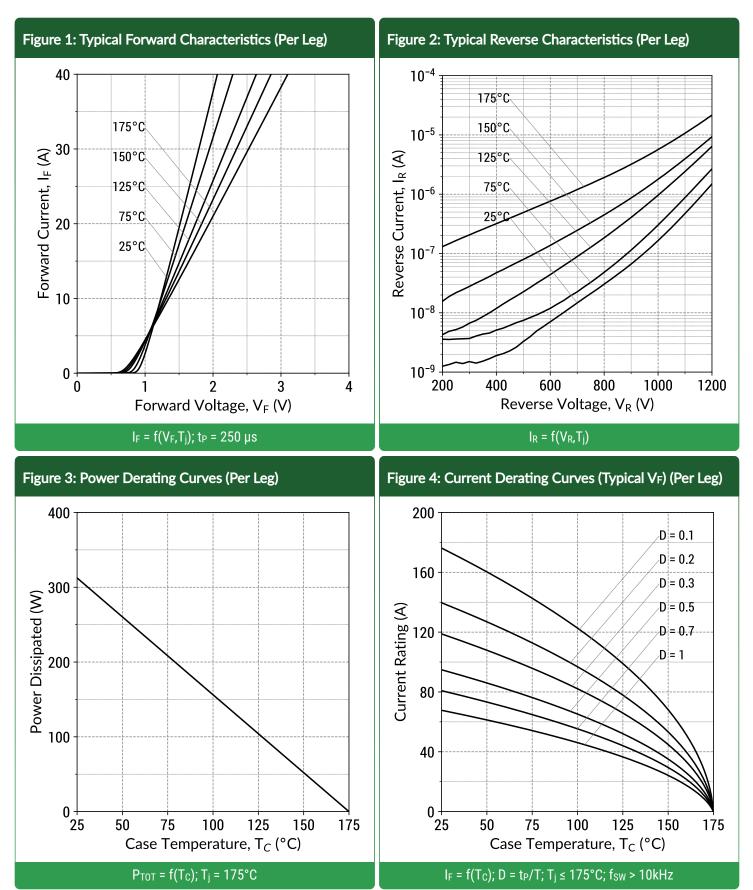
Deveneter	Cumbol	Conditions		Values			11	Nete
Parameter	Symbol			Min.	Тур.	Max.	Unit	Note
Diode Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 20 A, T <sub>j</sub> = 25°C			1.5	1.8	V	Fig. 1
Diode Forward Voltage	۷F	I <sub>F</sub> = 20 A, T <sub>j</sub> = 175°C			1.9			
Reverse Current	la la	V <sub>R</sub> = 1200 V, T <sub>j</sub> = 25°C			2	10	μA	Fig. 2
	I <sub>R</sub>	V <sub>R</sub> = 1200 V, T		22				
Total Capacitive Charge	0		V <sub>R</sub> = 400 V		74		nC	Fig. 7
	Qc	I <sub>F</sub> ≤ I <sub>F,MAX</sub>	V <sub>R</sub> = 800 V		107			
Switching Time	+	dl <sub>F</sub> /dt = 200 A/µs V <sub>R</sub> = 400 V		< 10		no		
	ts		V <sub>R</sub> = 800 V		× 10		ns	
Total Capacitance	С	V <sub>R</sub> = 1 V, f = 1MHz			1218		рĘ	Fig. 6
	U	V <sub>R</sub> = 800 V, f = 1MHz			71		pF	

### Thermal/Package Characteristics

Deremeter	Symbol	Conditions	Values			Unit	Note
Parameter		Conditions	Min.	Тур.	Max.	Unit	Note
Thermal Resistance, Junction - Case (Per Leg)	R <sub>thJC</sub>			0.48		°C/W	Fig. 9
Weight	WT			6.1		g	
Mounting Torque	T <sub>M</sub>	Screws to Heatsink			1.1	Nm	

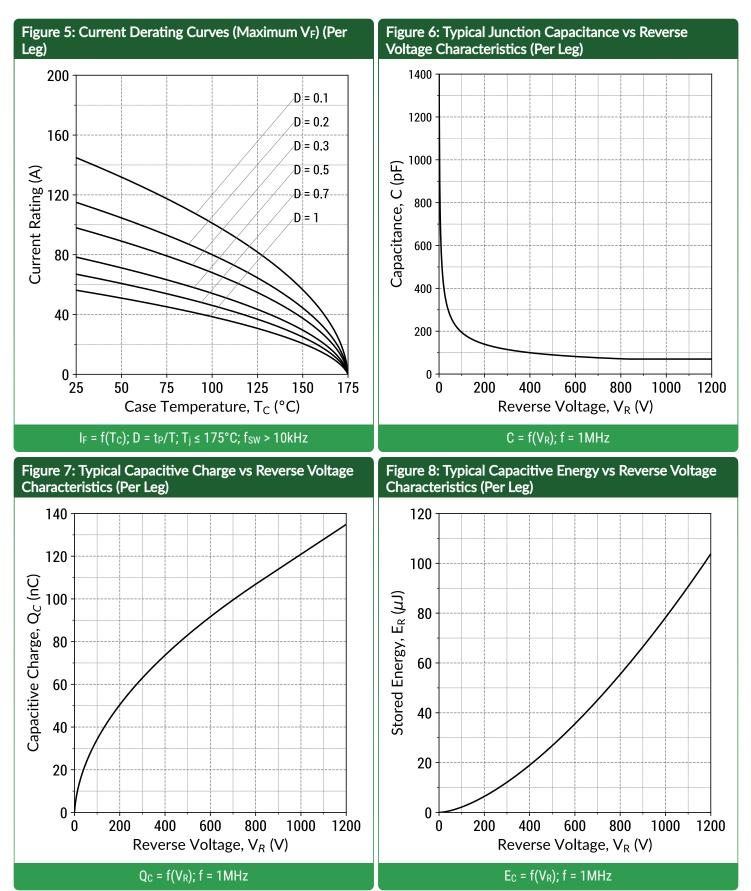
## GC2X20MPS12-247 1200V 40A SiC Schottky MPS<sup>™</sup> Diode





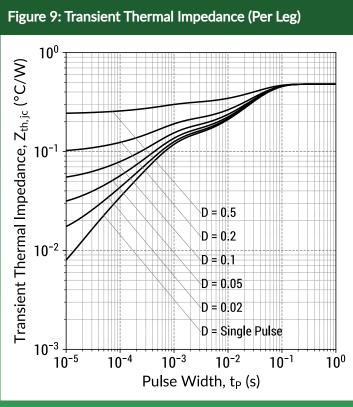
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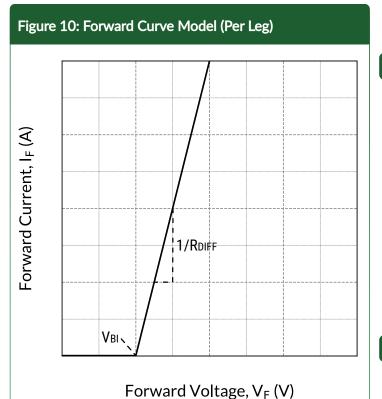


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 $Z_{th,jc} = f(t_P,D); D = t_P/T$ 



 $I_F = f(V_F, T_j)$ 

### Forward Curve Model Equation:

 $I_F = (V_F - V_{BI})/R_{DIFF} (A)$ 

Built-In Voltage (V<sub>BI</sub>):

 $V_{BI}(T_j) = m \times T_j + n (V)$ m = -0.00123 (V/°C) n = 0.995 (V)

Differential Resistance (RDIFF):

 $R_{DIFF}(T_j) = a \times T_j^2 + b \times T_j + c (\Omega)$ a = 5.96e-07 (\Omega/°C^2) b = 8.46e-05 (\Omega/°C) c = 0.0251 (\Omega)

Forward Power Loss Equation:

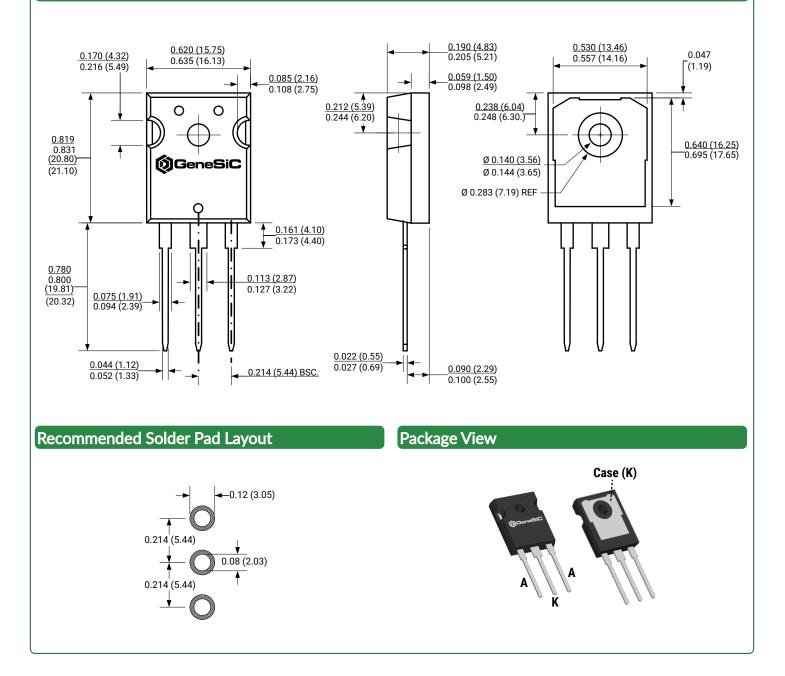
 $P_{LOSS} = V_{BI}(T_j) \times I_{AVG} + R_{DIFF}(T_j) \times I_{RMS}^2$ 

### GC2X20MPS12-247 1200V 40A SiC Schottky MPS<sup>™</sup> Diode



#### **Package Dimensions**

#### TO-247-3 Package Outline



#### NOTE

- 1. CONTROLLED DEIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
- 2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.



#### **RoHS Compliance**

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

### **REACH** Compliance

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a GeneSiC representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control systems.

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#### **Related Links**

SPICE Models:	https://www.genesicsemi.com/sic-schottky-mps/GC2X20MPS12-247/GC2X20MPS12-247_SPICE.zip
PLECS Models:	https://www.genesicsemi.com/sic-schottky-mps/GC2X20MPS12-247/GC2X20MPS12-247_PLECS.zip
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